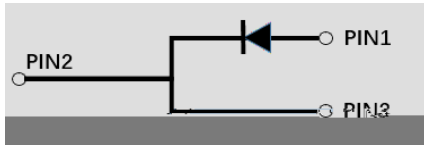
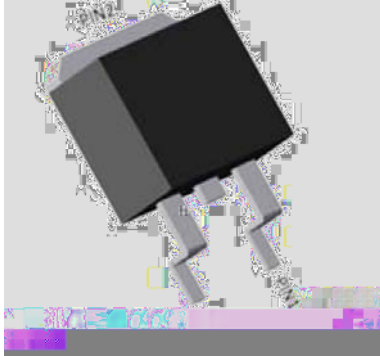


## Silicon Carbide Schottky Diode

$V_{RRM}$	650V
$I_F$ 135°C	14A
$Q_C$	30nC



### Features

- Positive temperature coefficient
- Temperature-independent switching
- Maximum working temperature at 175 °C
- Unipolar devices and zero reverse recovery current
- Zero forward recovery current
- Essentially no switching losses
- Reduction of heat sink requirements
- High-frequency operation
- Reduction of EMI

### Typical Applications

Typical applications are in power factor correction(PFC), solar inverter, uninterruptible power supply, motor drives, photovoltaic inverter, electric car and charger.

### Mechanical Data

**Package:** TO-263

Molding compound meets UL 94 V-0 flammability rating, RoHS-compliant, halogen-free

**Terminals:** Tin plated leads

**Polarity:** As marked

### Maximum Ratings ( $T_C=25$ Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	VALUE
Reverse Voltage (DC)	$V_{RRM}$	V	650
Reverse Voltage (DC) at $T_C=125$ °C	$V_{DC}$	V	650
Continuous Forward Current at $T_C=25$ °C	$I_F$	A	10
Continuous Forward Current at $T_C=175$ °C			1
Continuous Forward Current at $T_C=175$ °C (Peak)			10
Non-repetitive Peak Forward Surge Current at $T_C=125$ °C for $t_p \leq 10$ ms (Sine Wave)	$I_{FSM}$	A	10
Power Dissipation at $T_C=25$ °C	$P_{TOT}$	W	1.6
Power Dissipation at $T_C=175$ °C			0.5
Softening Value at $T_C=125$ °C for $t_p \leq 10$ ms	$Q_{rr}$	nC	30



# YJD106510BQG2

## Electrical Characteristics

PARAMETER	SYMBOL	UNIT	TEST CONDITIONS	Typ.	Max.
Forward voltage drop	$V_F$	V	$I_F=10A, T_J=25^{\circ}C$	1.35	1.55
			$I_F=10A, T_J=175^{\circ}C$	1.8	-
Reverse leakage current	$I_R$	$\mu A$	$V_R=650V, T_J=25^{\circ}C$	0.5	25
			$V_R=650V, T_J=175^{\circ}C$	2	-
Total capacitive charge	$Q_C$	nC	$V_R=400V, T_J=25^{\circ}C, Q_C=\int_0^{V_R} I_C(V)dV$	30	-
Total capacitance	C	pF	$V_R=0V, f=1MHZ$	543	-
			$V_R=200V, f=1MHZ$	55	-
			$V_R=400V, f=1MHZ$	52	-
Capacitance Stored Energy	$E_C$	$\mu J$	$V_R=400V$	3.7	-

## Thermal Characteristics ( $T_a=25$ Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	Value
Thermal resistance	$R_{J-C}$	$^{\circ}C/W$	1.1

## Typical Characteristics

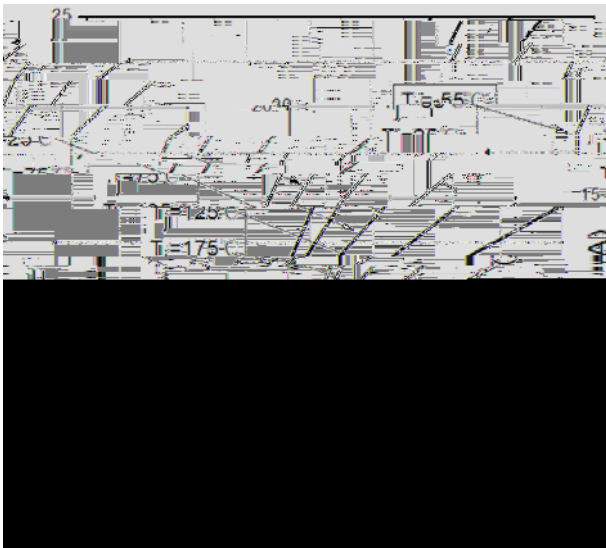


Figure 1. Forward Characteristics

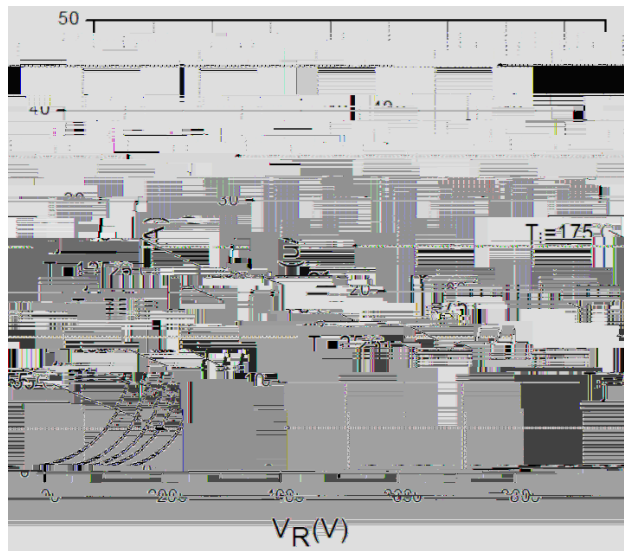


Figure 2. Reverse Characteristic



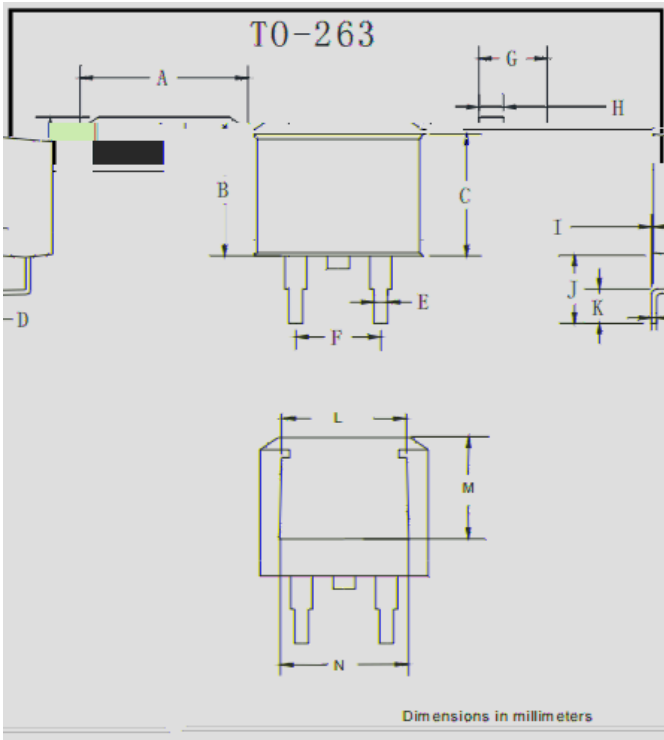
Figure 3. Capacitance vs. Reverse Voltage

Fig MM MM M I MM



# YJD106510BQG2

## Outline Dimensions



Dim	Min	Max
A	9.7	10.5
B	8.4	9.0
C	0.28	0.64
D	0.68	0.94
E	4.55	5.6
F	4.04	5.10
G	1.14	1.4
H	0	0.2
I	4.9	6.05
J	1.79	2.79
K	7.3	7.9
L	6.2	6.8
M	7.6	8.2
N		



## YJD106510BQG2

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